# **NPN POWER TRANSISTOR**

# BUX48A

### Features:

- Hermetic TO3 (TO-204AA) Metal Package
- High Voltage (HV) / High Current
- Ideally suited for HV power switching applications
- High Reliability Screening Options Available

#### Absolute Maximum Ratings (T<sub>c</sub> = 25°C unless otherwise noted)

V <sub>CER</sub>	Collector – Emitter Voltage	R <sub>BE</sub> = 10Ω 1000		
V <sub>CES</sub>	Collector – Emitter Voltage		1000V	
V <sub>CEO</sub>	Collector – Emitter Voltage		450V	
V <sub>EBO</sub>	Emitter – Base Voltage	7V		
۱ <sub>C</sub>	Collector Current – Continuous		15A	
IСМ	Collector Current – Peak	T <sub>P</sub> = 5ms	30A	
۱ <sub>B</sub>	Base Current		4A	
I <sub>BM</sub>	Base Current – Peak	T <sub>P</sub> = 5ms	20A	
PD	Total Power Dissipation at	T <sub>C</sub> = 25°C	175W	
		Derate Above 25°C	1.0W/°C	
Тj	Junction Temperature Range		-65 to +200°C	
T <sub>stg</sub>	Storage Temperature Range		-65 to +200°C	

## Thermal Properties (Tc= 25°C unless otherwise noted)

R <sub>ΘJC</sub> Thermal Resistance Junction to Case Max. 1.0°C/V	<sup>R</sup> ӨJС
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# **Electrical Specifications**

### Electrical Characteristics (Tc = 25° C unless otherwise noted)

SYMBOL	PARAMETER	TEST (	MIN	ТҮР	ΜΑΧ	UNITS	
V(BR)CEO <sup>(1)</sup>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA	I <sub>B</sub> = 0	450			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100μA	I <sub>C</sub> = 0	7		30	V
ICES	Collector Cut-Off Current	V <sub>CE</sub> = 1000V	V <sub>BE</sub> = 0			0.2	mA
			T <sub>C</sub> = +125°C			2	
ICER	Collector Cut-Off Current	V <sub>CE</sub> = 1000V	R <sub>BE</sub> = 10Ω			0.5	
			T <sub>C</sub> = +125°C			4	
I <sub>EBO</sub>	Emitter Cut-Off Current	V <sub>EB</sub> = 5V	I <sub>C</sub> = 0			1.0	
V <sub>CE(sat</sub> ) <sup>(1)</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A	I <sub>B</sub> = 1.6A			1.5	v
		I <sub>C</sub> = 12A	I <sub>B</sub> = 2.4A			5	
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A	I <sub>B</sub> = 1.6A			1.6	

## Dynamic Characteristics (Tc = 25° C unless otherwise noted)

SYMBOL	PARAMETER	TEST CONDITIONS			ТҮР	ΜΑΧ	UNITS
ton <sup>(2)</sup>	Turn-On Time	I <sub>C</sub> = 8A	V <sub>CC</sub> = 150V		0.8	1.0	
		I <sub>B1</sub> = 1.6A			0.0		
t <sub>f</sub> <sup>(2)</sup>	Fall Time	I <sub>C</sub> = 8A	V <sub>CC</sub> = 150V		0.4	0.8	μs
ts <sup>(2)</sup>	Storage Time	I <sub>B1</sub> = - I <sub>B2</sub> = 1.6A			2	3	

Notes

(1) Pulse Width  $\leq$  380us,  $\delta \leq$  2%

(2) By design, not a production test

General Note

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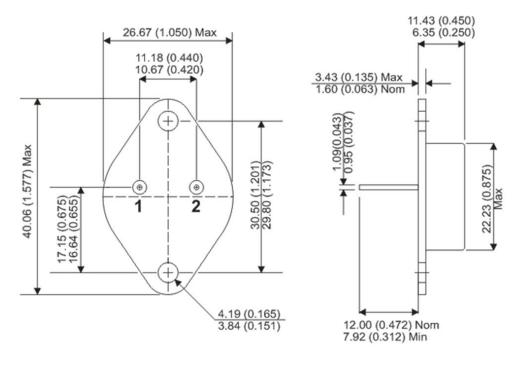
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# **Mechanical Data**

Dimensions in mm (Inches)



## TO3 (TO-204AA) METAL PACKAGE Underside View

Pin 1 - Base Pi

Pin 2 - Emitter Case - Collector

Lead Finish:

Hot solder dip (Sn63/Pb37) lead finish as standard. RoHS compliant options available but must be specified on purchase order.

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